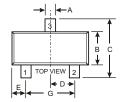


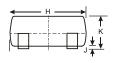
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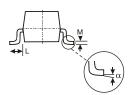
NPN SILICON EPITAXIAL PLANAR DIGITAL TRANSISTOR

Features

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors(see equivalent circuit)
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects
- Only the on/off conditions need to be set for operation,making device design easy
- Marking Code:E24







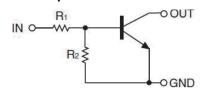
Dim	Min	Max				
Α	0.37	0.51				
В	1.20	1.40				
С	2.30	2.50				
D	0.89	1.03				
E	0.45	0.60				
G	1.78	2.05				
Н	2.80	3.00				
J	0.013	0.10				
K	0.903	1.10				
L	0.45	0.61				
M	0.085	0.180				
α	0°	8°				
All Dimensions in mm						

SOT-23

Maximum Ratings @ T_A = 25°C unless otherwise specified

Symbol	Parameter	Limits	Unit	
V _{cc}	Supply Voltage	50	V	
V _{IN}	Input Voltage	-10∼ + 40	V	
lo	Output Current	100	mA	
I _{CM}	Peak Collector Current	100	mA	
P _D	Power Dissipation	200	mW	
T _j	Junction Temperature	150	°C	
T _{stg}	Storage Temperature	-40~+150	°C	

Equivalent Circuit



1. IN 2. GND 3. OUT

Electrical Characteristics @ TA = 25°C unless otherwise specified

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input voltage	$V_{I(off)}$	V _{CC} =5V,I _O =100μA	0.5			V
	V _{I(on)}	V ₀ =0.3V,I ₀ =2mA			3	V
Output voltage	$V_{O(on)}$	I _O /I _I =10mA/0.5mA		0.1	0.3	V
Input current	l _l	V _I =5V			0.36	mA
Output current	I _{O(off)}	V _{CC} =50V,V _I =0			0.5	μA
DC current gain	Gı	V ₀ =5V,I ₀ =5mA	56			
Input resistance	R ₁		15.4	22	28.6	kΩ
Resistance ratio	R ₂ /R ₁		0.8	1	1.2	
Transition frequency	f⊤	Vo=10V,Io=5mA,f=100MHz		250		MHz





NPN SILICON EPITAXIAL PLANAR DIGITAL TRANSISTOR

TYPICAL TRANSIENT CHARACTERISTICS

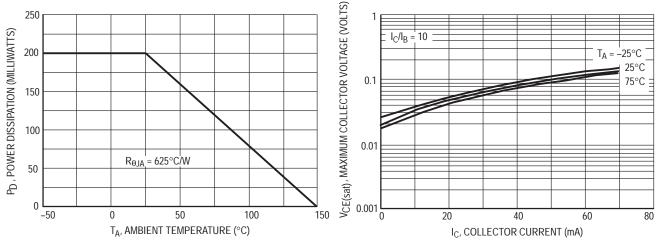


Figure 1. Derating Curve



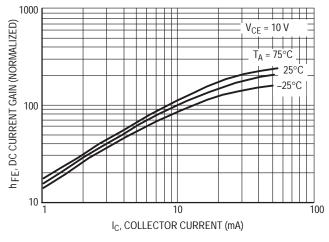


Figure 3. DC Current Gain

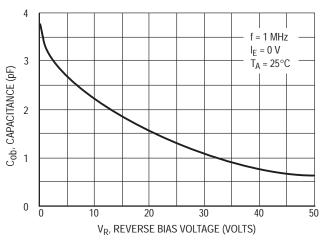


Figure 4. Output Capacitance

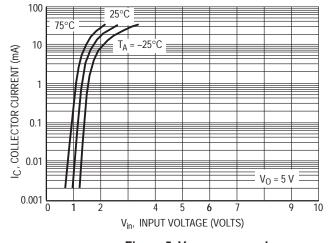


Figure 5. $V_{CE(sat)}$ versus I_C

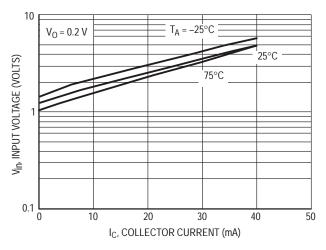


Figure 6. $V_{CE(sat)}$ versus I_C

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